**TOSHIBA** 2SA1586

# TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.

High Voltage and High current

:  $V_{CEO} = -50V$ , IC = -150mA (Max.)

Excellent her Linearity

 $: h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 \text{ (Typ.)}$ 

High h<sub>FE</sub>:  $h_{FE} = 70 \sim 400$ 

Low Noise: NF=1dB (Typ.), 10dB (Max.)

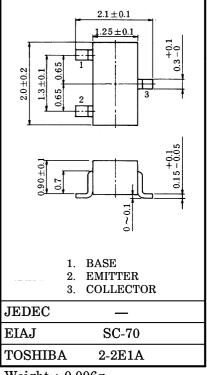
Complementary to 2SC4116

Small Package

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	-50	V
Collector-Emitter Voltage	$v_{CEO}$	-50	V
Emitter-Base Voltage	$v_{ m EBO}$	-5	V
Collector Current	$I_{\mathbf{C}}$	-150	mA
Base Current	$I_{\mathbf{B}}$	-30	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	100	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm



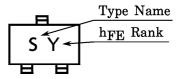
Weight: 0.006g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

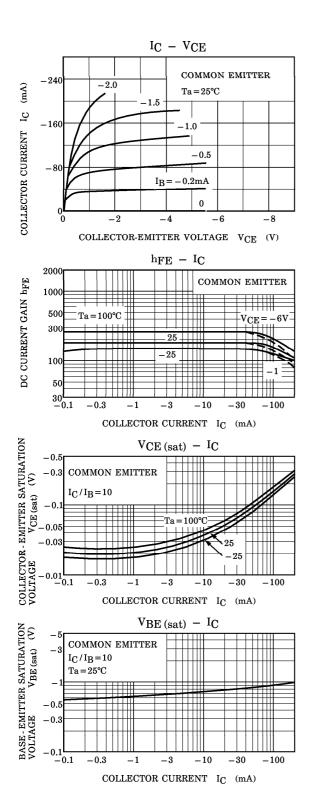
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{\mathrm{CBO}}$	$V_{CB} = -50V, I_{E} = 0$	_	_	-0.1	$\mu$ <b>A</b>
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_		-0.1	$\mu$ <b>A</b>
DC Current Gain	h <sub>FE</sub> (Note)	$V_{CE} = -6V, I_{C} = -2mA$	70	_	400	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$	_	-0.1	-0.3	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -10V, I_{C} = -1mA$	80	_	_	MHz
Collector Output Capacitance	Cob	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	4	7	pF
Noise Figure	NF	$V_{\text{CE}} = -6\text{V}, \text{ I}_{\text{C}} = -0.1\text{mA}, \\ f = 1\text{kHz}, \text{ Rg} = 10\text{k}\Omega$	_	1.0	10	dB

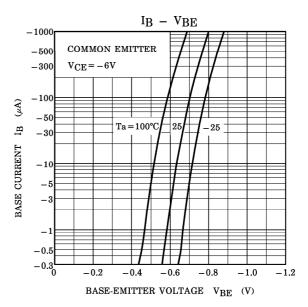
hFE Classification O(O): 70~140, Y(Y): 120~240, GR(G): 200~400 ( ) Marking Symbol Note:

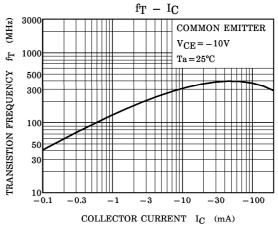
**MARKING** 

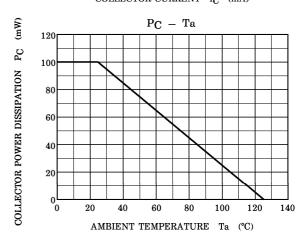


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